

L' Number	Hits	Search Text	DB	Time stamp
1	12	miyakawa.in. and plasma	EPO; JPO; DERWENT	2004/09/28 12:34
2	42	miyakawa.in. and plasma	USPAT; US-PGPUB	2004/09/28 12:40
6	5	(204/298.25.ccls.) and ((atmospheric high with pressure with cluster)	USPAT; US-PGPUB	2004/09/28 12:44
7	63	(atmospher\$3 with pressure with plasma) and (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2004/09/28 12:45
-	0	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and ((anneal\$3 heat\$s) with silylation with cur\$3)	USPAT; US-PGPUB	2003/05/13 11:25
-	0	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and ((anneal\$3 heat\$s) same silylation same cur\$3)	USPAT; US-PGPUB	2003/05/13 11:32
-	1	09/502,126	USPAT; US-PGPUB	2003/05/13 11:23
-	3534	atmospher\$3 with pressure with plasma	USPAT; US-PGPUB	2003/05/13 11:26
-	1709	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.	USPAT; US-PGPUB	2003/05/13 12:34
-	50	(atmospher\$3 with pressure with plasma) and (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2004/09/28 12:44
-	6	5578130.URPN.	USPAT	2003/05/13 11:30
-	3	((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.) and ((anneal\$3 heat\$s) same silicon same cur\$3)	USPAT; US-PGPUB	2003/05/13 11:34
-	49	(cur\$3 with chamber) and (anneal\$3 with chamber) and ((silicon silylation) with chamber)	USPAT; US-PGPUB	2003/05/13 12:17
-	8	("4944895" "5047369" "5858457" "5958577" "6048804" "6153511" "6218302" "6284682").PN.	USPAT	2003/05/13 11:57
-	1	"high pressure deposition module"	USPAT; US-PGPUB	2003/05/13 12:33
-	1374	"APCVD"	USPAT; US-PGPUB	2003/05/13 12:39
-	17	"APCVD" and (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 12:34
-	464	"APCVD" with plasma	USPAT; US-PGPUB	2003/05/13 12:42
-	1	("APCVD" with plasma) and (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 12:39
-	9	"silylation chamber"	USPAT; US-PGPUB	2003/05/13 12:44
-	44	silylation with chamber	USPAT; US-PGPUB	2003/05/13 12:44
-	35	(silylation with chamber) not "silylation chamber"	USPAT; US-PGPUB	2003/05/13 13:05
-	1	("6451118").PN.	USPAT; US-PGPUB	2003/05/13 13:05
-	1667	spin with coating with uniform\$3	USPAT; US-PGPUB	2003/05/13 15:34
-	5	(spin with coating with uniform\$3) and (((118/719) or (156/345.31) or (156/345.32) or (414/939)).CCLS.)	USPAT; US-PGPUB	2003/05/13 15:37
-	0	spin with coating with uniform\$3 with atmospheric with deposit\$3	USPAT; US-PGPUB	2003/05/13 15:35
-	0	spin with coating with uniform\$3 same (atmospheric with deposit\$3)	USPAT; US-PGPUB	2003/05/13 15:36
-	162	(spin with coating with uniform\$3) and (118/\$.ccls.)	USPAT; US-PGPUB	2003/05/13 15:40
-	4	(spin with coating with uniform\$3 with atmospheric) and (118/\$.ccls.)	USPAT; US-PGPUB	2003/05/13 15:40
-	3584	plasma with (atmospheric high) with pressure	EPO; JPO; DERWENT	2003/11/18 11:15

-	1257	plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)	EPO; JPO; DERWENT	2003/11/18 11:29
-	380	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and c23c016\$.ipc.	EPO; JPO; DERWENT	2003/11/18 11:30
-	135	(plasma with (atmospheric) with pressure with (coat\$3 deposit\$3 layer film)) and c23c016\$.ipc.	EPO; JPO; DERWENT	2003/11/18 12:17
-	30	(plasma with (atmospheric) with pressure with (coat\$3 deposit\$3 layer film) with (semiconductor dielectric)) and c23c016\$.ipc.	EPO; JPO; DERWENT	2003/11/18 11:20
-	3232	plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)	USPAT; US-PGPUB	2003/11/18 11:29
-	20	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 118/\$.ccls.	EPO; JPO; DERWENT	2003/11/18 12:59
-	330	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 118/\$.ccls.	USPAT; US-PGPUB	2003/11/18 12:59
-	2	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 414/\$.ccls.	USPAT; US-PGPUB	2003/11/18 11:31
-	135	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 156/345\$.ccls.	USPAT; US-PGPUB	2003/11/18 11:31
-	41	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 118/719.ccls.	USPAT; US-PGPUB	2003/11/18 11:31
-	1	("5319247").PN.	USPAT; US-PGPUB	2003/11/18 11:53
-	33	5319247.URPN.	USPAT	2003/11/18 11:45
-	1154	"atmospheric pressure" with plasma with (deposit\$3 coat\$3 film layer)	USPAT; US-PGPUB	2003/11/18 11:54
-	376	"atmospheric pressure" with plasma with (deposit\$3 coat\$3 film layer)	EPO; JPO; DERWENT	2003/11/18 11:54
-	34	("atmospheric pressure" with plasma with (deposit\$3 coat\$3 film layer)) same semiconductor	EPO; JPO; DERWENT	2003/11/18 11:54
-	215	("atmospheric pressure" with plasma with (deposit\$3 coat\$3 film layer)) same semiconductor	USPAT; US-PGPUB	2003/11/18 11:59
-	330	(plasma with (atmospheric high) with pressure with (coat\$3 deposit\$3 layer film)) and 118/\$.ccls.	USPAT; US-PGPUB	2003/11/18 12:17
-	2	(in\$lline same cluster) and c23c016\$.ipc.	EPO; JPO; DERWENT	2003/11/18 12:18
-	9	(in\$lline same cluster) and 118/719.ccls.	USPAT; US-PGPUB	2003/11/18 12:18
-	24	(plasma with "atmospheric pressure") and 118/719.ccls.	USPAT; US-PGPUB	2003/11/18 13:53
-	18	5651867.URPN.	USPAT	2003/11/18 13:07
-	1	("6342275").PN.	USPAT; US-PGPUB	2003/11/18 14:56
-	3	"18249"	EPO; JPO; DERWENT	2003/11/18 14:56
-	669	miyakawa.in.	EPO; JPO; DERWENT	2003/11/18 14:56
-	10	miyakawa.in. and plasma	EPO; JPO; DERWENT	2004/09/28 12:34
-	26	barnes-michael.in. cox-michael-s\$.in. lai-canfeng.in. parks-joun.in.	EPO; JPO; DERWENT	2003/11/18 15:02
-	58	barnes-michael.in. cox-michael-s\$.in. lai-canfeng.in. parks-joun.in.	USPAT; US-PGPUB	2003/11/18 15:02
-	10	"electromagnetic wave marker"	EPO; JPO; DERWENT	2003/11/18 16:48
-	1	"electromagnetic wave marker"	USPAT; US-PGPUB	2003/11/18 16:49
-	0	"electromagnetic wave" with lane\$1marker	USPAT; US-PGPUB	2003/11/18 16:49

-	27	"electromagnetic wave" with lane	USPAT; US-PGPUB	2003/11/18 16:50
-	9	plasma and ((atmospheric ambient high) with pressure with cluster)	EPO; JPO; DERWENT	2004/06/08 15:53
-	22	plasma and ((atmospheric ambient high) with pressure) and cluster	EPO; JPO; DERWENT	2004/06/08 15:53
-	3747	plasma and ((atmospheric ambient high) with pressure) and cluster	USPAT; US-PGPUB	2004/06/08 15:53
-	847	(plasma same ((atmospheric ambient high) with pressure)) and cluster	USPAT; US-PGPUB	2004/06/08 15:54
-	36	(plasma same ((atmospheric ambient high) with pressure)) same (cluster with (tool apparatus))	USPAT; US-PGPUB	2004/06/08 16:23
-	14	("4312626" "4390322" "4484861" "4523897" "4640667" "4718836" "5009575" "5165864" "5238362" "5672322" "5803713" "5820354" "5871336" "6179573").PN.	USPAT	2004/06/08 16:03
-	0	6736606.URPN.	USPAT	2004/06/08 16:12
-	0	"apcvd" same cluster same plasma	USPAT; US-PGPUB	2004/06/08 16:24
-	0	"apcvd" same cluster same plasma	EPO; JPO; DERWENT	2004/06/08 16:24
-	14	"apcvd" same plasma	EPO; JPO; DERWENT	2004/06/08 16:25
-	825	"apcvd" same plasma	USPAT; US-PGPUB	2004/06/08 16:25
-	7	"apcvd" same plasma same ((cluster)((multiple plural\$3 several) with (chamber apparatus units)))	USPAT; US-PGPUB	2004/06/08 16:31
-	728676	("apcvd" same plasma) and (silicon and valley).as. ((cluster)((multiple plural\$3 several) with (chamber apparatus units)))	USPAT; US-PGPUB	2004/06/08 16:32
-	7	("apcvd" same plasma) and (silicon and valley).as.	USPAT; US-PGPUB	2004/06/08 16:32
-	7	("apcvd" same plasma) and (valley).as.	USPAT; US-PGPUB	2004/06/08 16:32
-	1	("6143080").PN.	USPAT; US-PGPUB	2004/06/09 13:15
-	2	((("4834020") or ("5136975")).PN.	USPAT; US-PGPUB	2004/06/09 13:15
-	10	("4834020" "5136975" "5413671" "5683516" "5776254" "5849088" "5863337" "5888579" "5976258" "6022414").PN.	USPAT	2004/06/09 13:17
-	1	("6451118").PN.	USPAT; US-PGPUB	2004/06/09 15:53
-	5	118/718.ccls. and (spin with coat\$3)	USPAT; US-PGPUB	2004/06/09 15:05
-	42	(US-5863338-\$ or US-5626677-\$ or US-5587207-\$ or US-5578130-\$ or US-6559070-\$ or US-6562128-\$ or US-6338756-\$ or US-6001739-\$ or US-6451118-\$ or US-5743965-\$ or US-5562772-\$ or US-5099782-\$ or US-4640846-\$ or US-5319247-\$ or US-6342275-\$ or US-6143080-\$ or US-5605867-\$ or US-5484749-\$ or US-5041304-\$ or US-4003770-\$ or US-6207005-\$ or US-6627039-\$ or US-6736606-\$ or US-6026589-\$ or US-5776254-\$).did. or (US-20030039766-\$ or US-20020134310-\$ or US-20020197878-\$ or US-20030106791-\$ or US-20030044154-\$).did. or (WO-9518249-\$).did. or (JP-2001168029-\$ or JP-2001035835-\$ or JP-08298245-\$ or JP-06330326-\$ or JP-06041755-\$ or JP-01306569-\$ or JP-08203891-\$).did. or (EP-678914-\$ or DE-4135810-\$ or EP-431951-\$ or US-6342275-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/09 15:20

-	0	((US-5863338-\$ or US-5626677-\$ or US-5587207-\$ or US-5578130-\$ or US-6559070-\$ or US-6562128-\$ or US-6338756-\$ or US-6001739-\$ or US-6451118-\$ or US-5743965-\$ or US-5562772-\$ or US-5099782-\$ or US-4640846-\$ or US-5319247-\$ or US-6342275-\$ or US-6143080-\$ or US-5605867-\$ or US-5484749-\$ or US-5041304-\$ or US-4003770-\$ or US-6207005-\$ or US-6627039-\$ or US-6736606-\$ or US-6026589-\$ or US-5776254-\$).did. or (US-20030039766-\$ or US-20020134310-\$ or US-20020197878-\$ or US-20030106791-\$ or US-20030044154-\$).did. or (WO-9518249-\$).did. or (JP-2001168029-\$ or JP-2001035835-\$ or JP-08298245-\$ or JP-06330326-\$ or JP-06041755-\$ or JP-01306569-\$ or JP-08203891-\$).did. or (EP-678914-\$ or DE-4135810-\$ or EP-431951-\$ or US-6342275-\$).did.) and imahashi.in.	USPAT; US-PGPUB	2004/06/09 15:20
-	2	118/719.ccls. and imahashi.in.	USPAT; US-PGPUB	2004/06/09 15:24
-	10	118/719.ccls. and ((atmospheric high) with pressure with cluster)	USPAT; US-PGPUB	2004/06/09 15:25
-	5	(204/298.25.ccls.) and ((atmospheric high) with pressure with cluster)	USPAT; US-PGPUB	2004/09/28 12:44
-	1	("6143080").PN.	USPAT; US-PGPUB	2004/06/09 16:00
-	2	((("5683516") or ("5849088"))).PN.	USPAT; US-PGPUB	2004/06/09 16:00